

# 2SB621, 2SB621A

Silicon PNP epitaxial planer type

For low-frequency output amplification

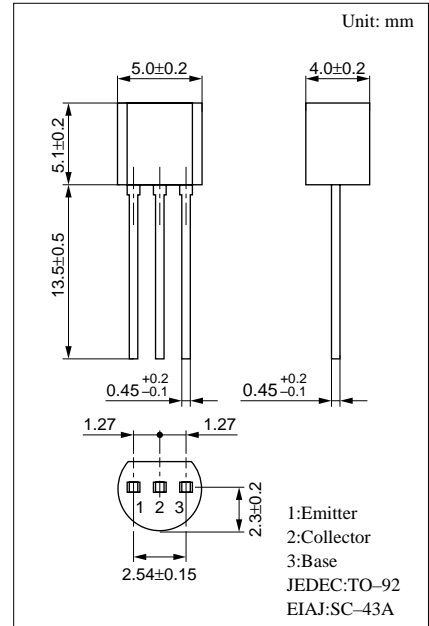
Complementary to 2SD592 and 2SD592A

## Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$ .
- High transition frequency  $f_T$ .

## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rated	Unit
Collector to base voltage	$V_{CBO}$	-30	V
2SB621A		-60	
Collector to emitter voltage	$V_{CEO}$	-25	V
2SB621A		-50	
Emitter to base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-1.5	A
Collector current	$I_C$	-1	A
Collector power dissipation	$P_C$	750	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C



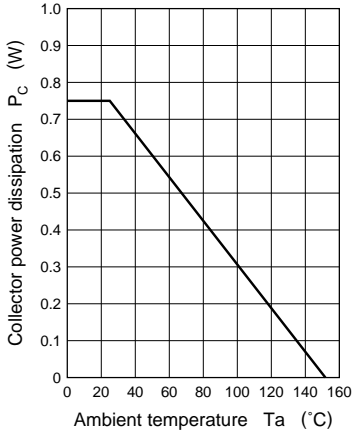
## Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -20V, I_E = 0$			-0.1	$\mu A$
Collector to base voltage	$V_{CBO}$	$I_C = -10\mu A, I_E = 0$	-30			V
			-60			
Collector to emitter voltage	$V_{CEO}$	$I_C = -2mA, I_B = 0$	-25			V
			-50			
Emitter to base voltage	$V_{EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE1}^*$	$V_{CE} = -10V, I_C = -500mA$	85		340	
	$h_{FE2}$	$V_{CE} = -5V, I_C = -1A$	50			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.2	-0.4	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.85	-1.2	V
Transition frequency	$f_T$	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	30	pF

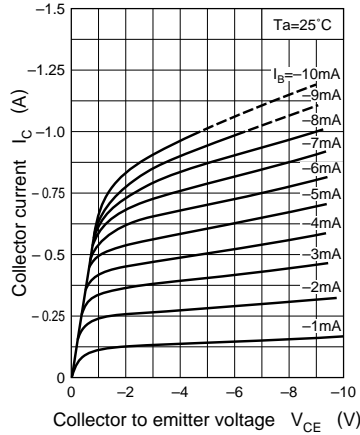
\* $h_{FE1}$  Rank classification

Rank	Q	R	S
$h_{FE1}$	85 ~ 170	120 ~ 240	170 ~ 340

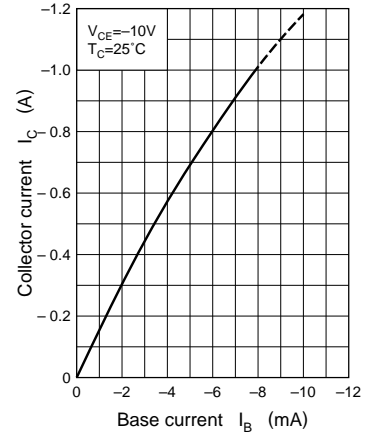
$P_C - T_a$



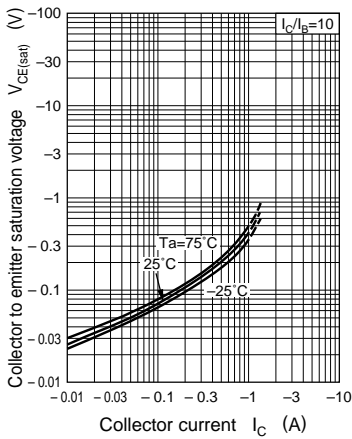
$I_C - V_{CE}$



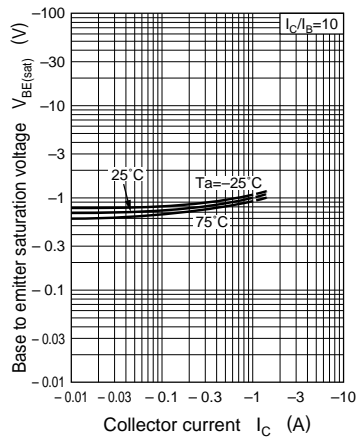
$I_C - I_B$



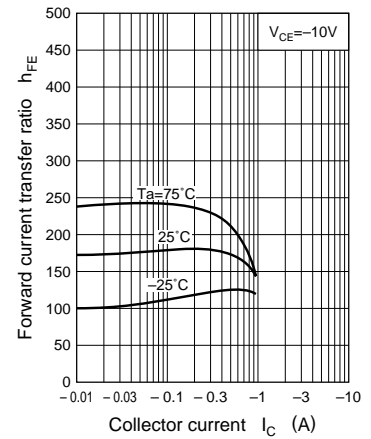
$V_{CE(sat)} - I_C$



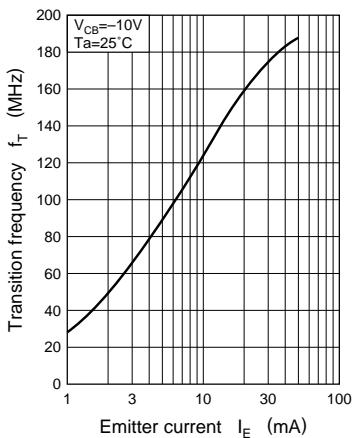
$V_{BE(sat)} - I_C$



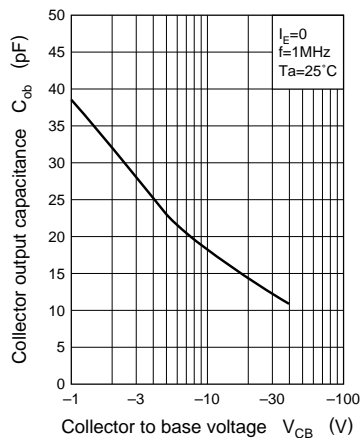
$h_{FE} - I_C$



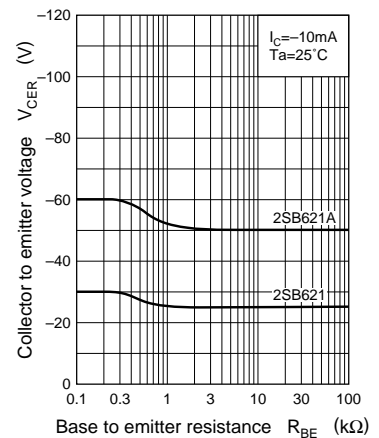
$f_T - I_E$



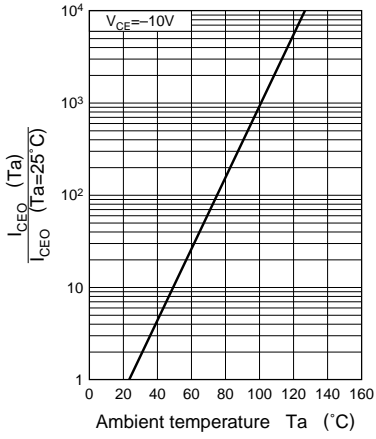
$C_{ob} - V_{CB}$



$V_{CER} - R_{BE}$



$I_{CEO} - T_a$



Area of safe operation (ASO)

